

Electronic Supplementary Information

Vertical junction photodetectors based on reduced graphene oxide/silicon Schottky diodes

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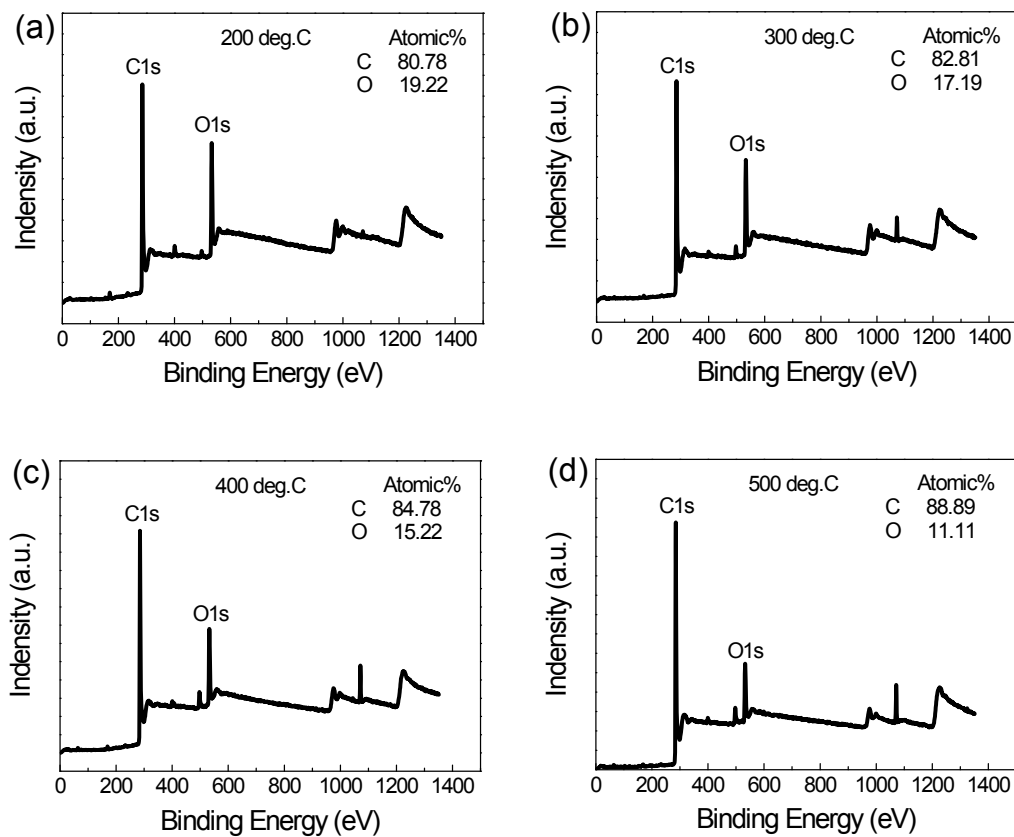
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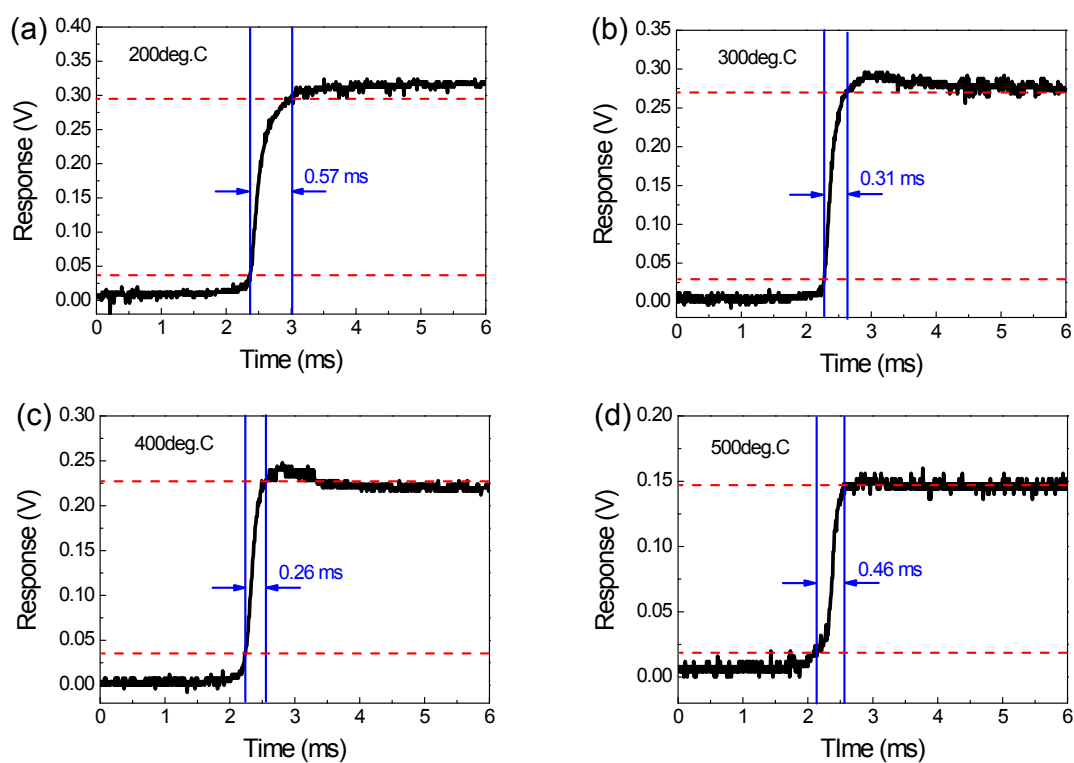
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This file includes:

Figures S1~S3.



FigureS1. X-ray photoelectron spectra of RGO films annealed at different temperatures. The oxygen content decreases apparently with higher temperature.



FigureS2. Responses of the devices at different reduction levels. The response time was calculated from 10% to 90% of their peak values.

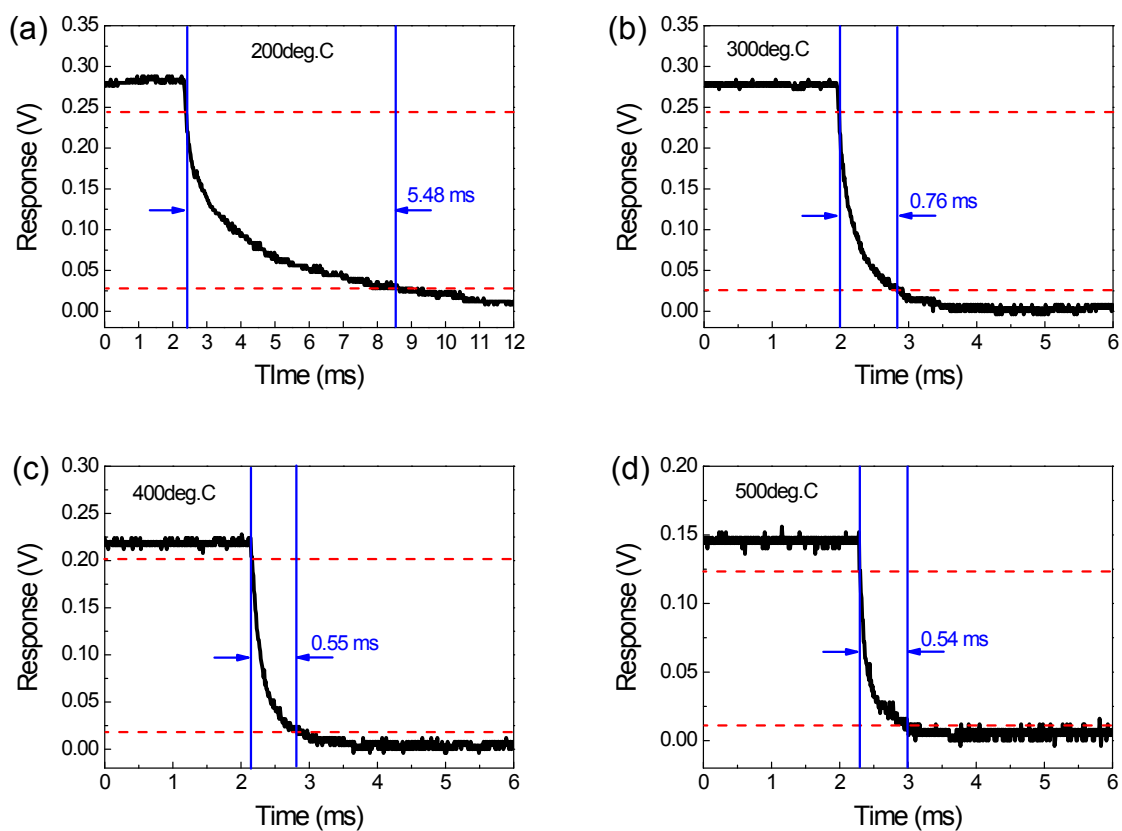


Figure S3. Recovery process of the devices at different reduction levels. The recovery time was calculated from 90% to 10% of their peak values.